Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2577	438/257	USPAT	OR	ON	2005/03/03 13:51
L2	1445	438/258	USPAT	OR	ON	2005/03/03 13:51
L3	946	438/259	USPAT	OR	ON	2005/03/03 13:51
L4	346	438/260	USPAT	OR.	ON	2005/03/03 13:51
L5	927	438/261	USPAT	OR	ON	2005/03/03 13:51
L6	531	438/262	USPAT	OR	ON	2005/03/03 13:51
L7	600	438/263	USPAT	OR	ON	2005/03/03 13:51
L8	1445	438/264	USPAT	OR	ON	2005/03/03 13:51
L9	465	438/265	USPAT	OR	ON	2005/03/03 13:51
L10	854	438/266	USPAT	OR.	ON	2005/03/03 13:51
L11	568	438/267	USPAT	OR	ON	2005/03/03 13:52
L12	600	438/263	USPAT	OR	ON	2005/03/03 13:52
L13	1445	438/264	USPAT	OR	ON	2005/03/03 13:53
L14	1	("5969384").PN.	USPAT	OR	OFF	2005/03/03 13:53
L15	1	14 and (flash or memory or floating or control or gate or electrode or SiO$ or polysilicon or oxide or silicon or intergate or dielectric or tunnel or conduction or band or energy or level or first or second or source or drain or region or HfO or YO or AlO or ZrO or mask or ion or implantation or implanting)	USPAT	OR	ON	2005/03/03 13:54
L16	1	("6287988").PN.	USPAT	OR.	OFF	2005/03/03 13:54
L17	1	16 and (flash or memory or floating or control or gate or electrode or SiO$ or polysilicon or oxide or silicon or intergate or dielectric or tunnel or conduction or band or energy or level or first or second or source or drain or region or HfO or YO or AlO or ZrO or mask or ion or implantation or implanting)	USPAT	OR	ON	2005/03/03 13:54
S116	1	("6456535").PN.	USPAT	OR	OFF	2005/03/03 10:42
S117	1	("6384448").PN.	USPAT	OR	OFF	2005/03/03 10:44
S118	27	flash and memory and floating and control and gate and electrode and SiO$ and polysilicon and oxide and silicon and (intergate adj dielectric) and (tunnel adj oxide)	USPAT	OR	ON	2005/03/03 10:48

S11 9	1	flash and memory and floating and control and gate and electrode and SiO$ and polysilicon and oxide and silicon and (intergate adj dielectric) and (tunnel adj oxide) and (conduction adj band adj energy adj level)	USPAT	OR	ON	2005/03/03 10:57
S12 0	1	S116 and (flash or memory or floating or control or gate or electrode or SiO$ or polysilicon or oxide or silicon or intergate or dielectric or tunnel or conduction or band or energy or level or first or second or source or drain or region or HfO or YO or AlO or ZrO or mask or ion or implantation or implanting)	USPAT	OR	ON	2005/03/03 11:12
S12 1	1	S117 and (flash or memory or floating or control or gate or electrode or SiO$ or polysilicon or oxide or silicon or intergate or dielectric or tunnel or conduction or band or energy or level or first or second or source or drain or region or HfO or YO or AlO or ZrO or mask or ion or implantation or implanting)	USPAT	OR	ON	2005/03/03 11:17
S12 2	1	"6096640".PN.	USPAT; USOCR	OR	ON	2005/03/03 11:15
S12 3	1	"6063668".PN.	USPAT; USOCR	OR	ON	2005/03/03 11:16
S12 4	1	"5796670".PN.	USPAT; USOCR	OR	ON	2005/03/03 11:16
S12 5	1	S124 and (flash or memory or floating or control or gate or electrode or SiO$ or polysilicon or oxide or silicon or intergate or dielectric or tunnel or conduction or band or energy or level or first or second or source or drain or region or HfO or YO or AlO or ZrO or mask or ion or implantation or implanting)	USPAT	OR	ON	2005/03/03 11:23
S12 6	1	("6781876").PN.	USPAT	OR	OFF	2005/03/03 11:22

| S12 7 | 1 | S126 and (flash or memory or floating or control or gate or electrode or SiO$ or polysilicon or oxide or silicon or intergate or dielectric or tunnel or conduction or band or energy or level or first or second or source or drain or region or HfO or YO or AlO or ZrO or mask or ion or implantation or implanting) | USPAT | OR | ON | 2005/03/03 13:53 |
| S12 8 | 12 | (tunnel adj oxide) and (first adj tunnel adj oxide) and (second adj tunnel adj oxide) and floating and control and gate and polysilicon and memory | USPAT | OR | ON | 2005/03/03 13:50 |